

**GENERAL DESCRIPTION**

The 2003 is a common base transistor capable of providing 3 Watts of CW RF output power in the 1000-2000 MHz. This hermetically sealed transistor is specifically designed for Class C amplifier applications. It utilizes gold metallization and diffused ballasting to provide high reliability and supreme ruggedness.

**2003**  
**3 WATTS - 28 VOLTS**  
**2000 MHz**

**MICROWAVE CW BIPOLAR**

**ABSOLUTE MAXIMUM RATINGS**

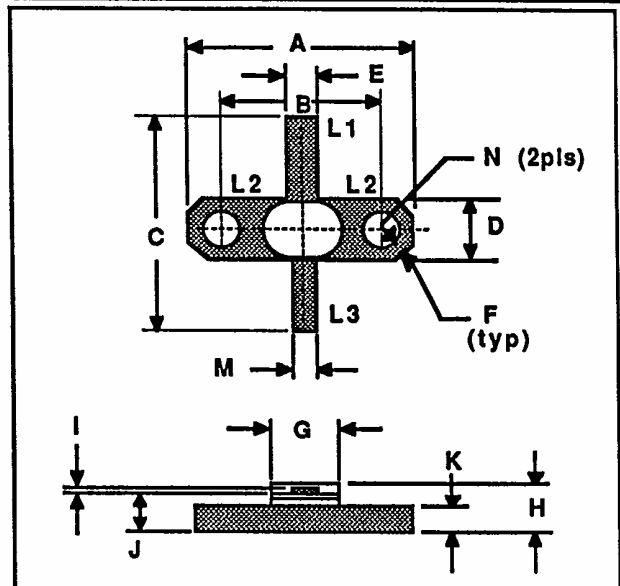
Maximum Power Dissipation @ 25°C Case Temperature **11.6 W**

**Maximum Voltage and Current**

BVces Collector to Emitter Voltage **50 V**  
 BVebo Emitter to Base Voltage **3.5 V**  
 Ic Collector Current **0.5 A**

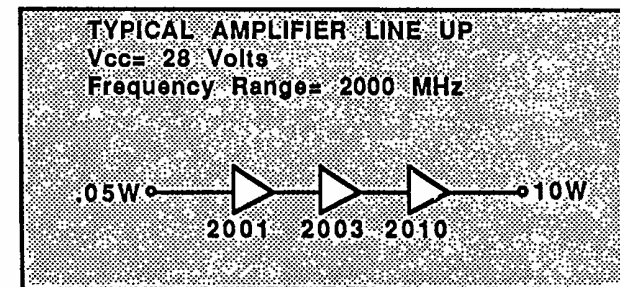
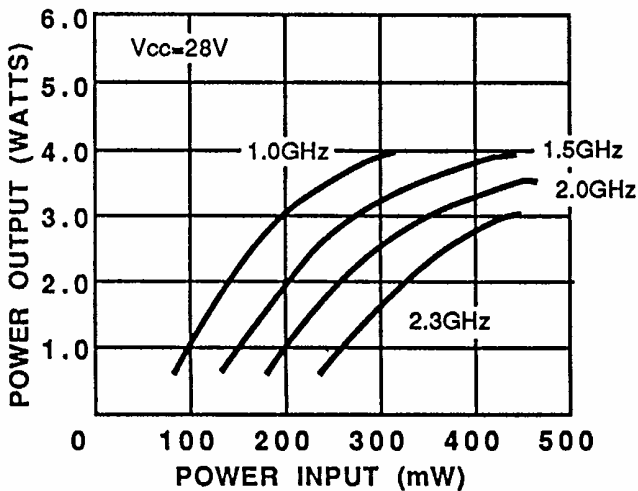
**Maximum Temperatures**

Storage Temperature **-65 to +200°C**  
 Operating Junction Temperature **+200°C**



DIM	Millimeter	TOL	Inches	TOL
L1 : B				
L2 : E				
L3 : C				
A	20.32	.13	.800	.005
B	14.27	.13	.562	.005
C	18.03	MIN	.710	MIN
D	5.84	.13	.230	.005
E	3.05	.13	.120	.005
F	45°	5°	45°	5°
G	5.84	.13	.230	.005
H	4.57	REF	.180	REF
I	0.13	.02	.005	.001
J	3.81	.13	.150	.005
K	1.52	.13	.060	.005
M	1.27	.13	.050	.005
N	3.30	.13	.130	.005

**POWER OUTPUT VS POWER INPUT (TYPICAL)**

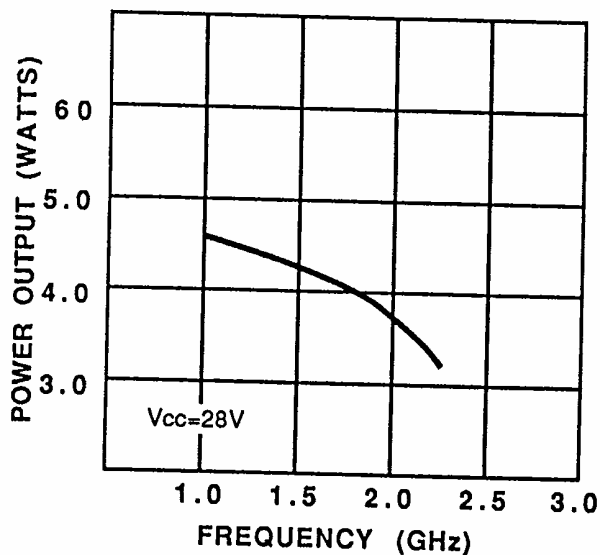


**ELECTRICAL CHARACTERISTICS<sup>1</sup>**

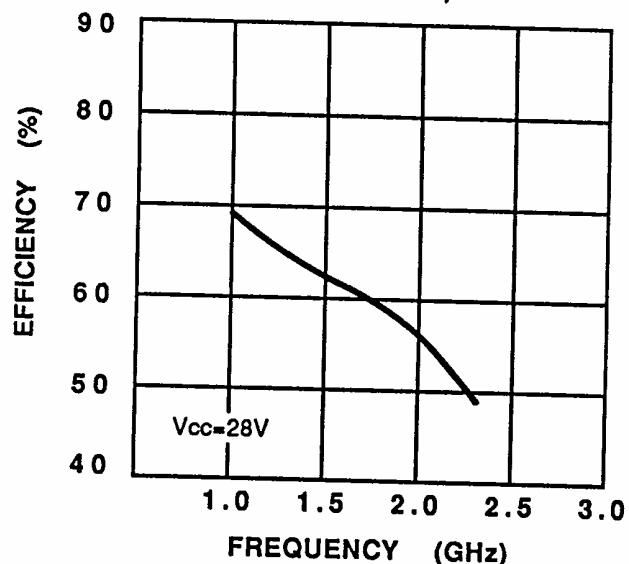
SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
P <sub>out</sub>	Power Output	f= 2000 MHz V <sub>cc</sub> = 28V P <sub>in</sub> = 0.47W	3.0			Watts
P <sub>in</sub>	Power Input				0.47	Watts
P <sub>g</sub>	Power Gain		8.1			dB
η <sub>c</sub>	Collector Efficiency		40			%
V <sub>SWR</sub>	Load Mismatch Tolerance				∞:1	
B <sub>Vebo</sub>	Breakdown Voltage (Emitter to Base)	I <sub>c</sub> = 0A, I <sub>e</sub> = 1.0mA	3.5			Volts
B <sub>Vces</sub>	Breakdown Voltage (Collector to Emitter)	V <sub>be</sub> = 0A, I <sub>c</sub> = 10mA	50			Volts
B <sub>Vcbo</sub>	Breakdown Voltage (Collector - Base)	I <sub>e</sub> = 0A, I <sub>c</sub> = 1mA	45			Volts
I <sub>cbo</sub>	Collector Leakage Current	I <sub>e</sub> = 0A, V <sub>cb</sub> =28V			500	μA
C <sub>ob</sub>	Capacitance-Collector to Base	f= 1MHz, V <sub>cb</sub> = 28V		5.0		pF
h <sub>FE</sub>	DC-Current Gain	V <sub>ce</sub> = 5V, I <sub>c</sub> = 100mA	10			
θ <sub>jc</sub>	Thermal Resistance	T <sub>f</sub> = 25°C			15	°C/W

NOTE 1: T<sub>c</sub> = 25°C unless otherwise specified.

**POWER OUTPUT VS FREQUENCY (TYPICAL)**



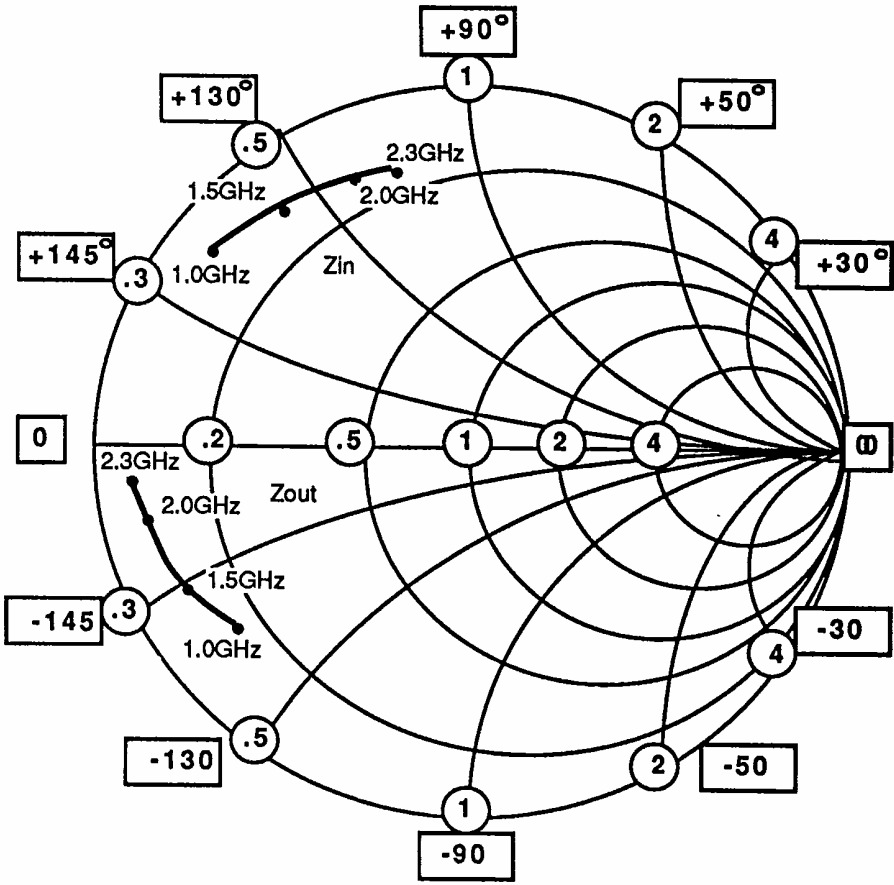
**EFFICIENCY VS FREQUENCY (TYPICAL)**



SPECIFICATIONS MAY BE SUBJECT TO CHANGE WITHOUT NOTICE

# SMITH CHART 2003

**NORMALIZED IMPEDANCE AND ADMITTANCE COORDINATES**



**NORMALIZED TO A 50 OHM SYSTEM.**